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2SC1214

Silicon NPN Epitaxial

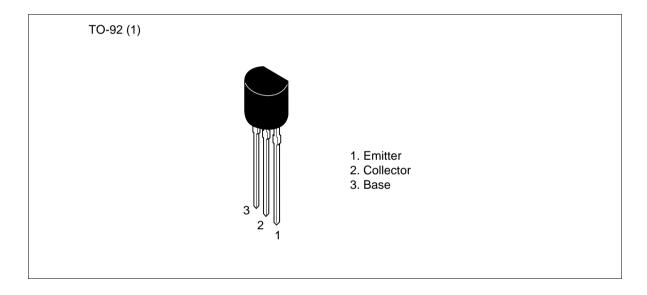


ADE-208-1050 (Z) 1st. Edition Mar. 2001

Application

Low frequency amplifier

Outline



2SC1214

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	50	V
Collector to emitter voltage	V _{CEO}	50	V
Emitter to base voltage	$V_{\scriptscriptstyle{EBO}}$	4	V
Collector current	I _c	500	mA
Collector power dissipation	P _c	600	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

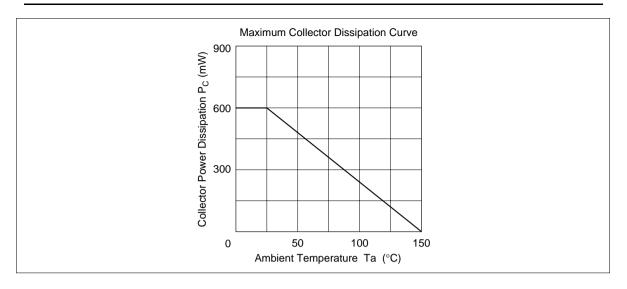
Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	50	_	_	V	$I_{c} = 10 \ \mu A, \ I_{e} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	50	_	_	V	$I_C = 1 \text{ mA}, R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	4	_	_	V	$I_{E} = 10 \ \mu A, \ I_{C} = 0$
Collector cutoff current	I _{CBO}		_	0.5	μA	$V_{CB} = 20 \text{ V}, I_{E} = 0$
DC current transfer ratio	h _{FE} *	60	_	320		$V_{CE} = 3 \text{ V}, I_{C} = 10 \text{ mA}$
	h _{FE}	10	_	_		$V_{CE} = 3 \text{ V}, I_{C} = 500 \text{ mA}$ (pulse test)
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	0.2	0.6	V	I_C = 150 mA, I_B = 15 mA (Pulse test)
Base to emitter voltage	V _{BE}	_	0.64	_	V	$V_{CE} = 3 \text{ V}, I_{C} = 10 \text{ mA}$

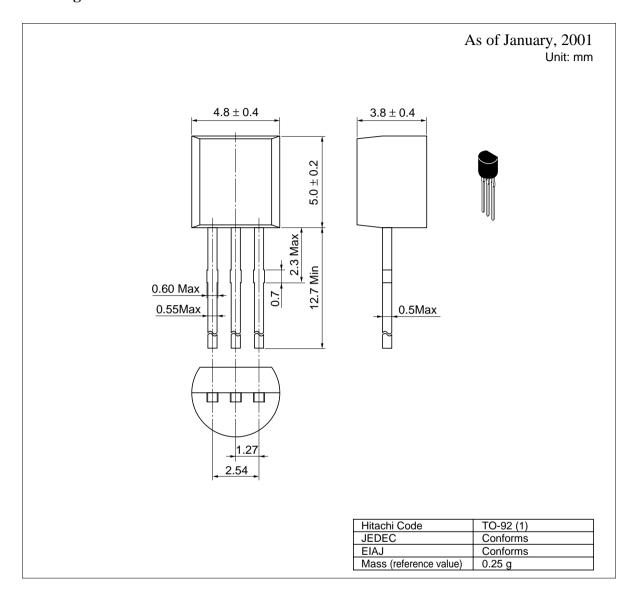
Note: 1. The 2SC1214 is grouped by h_{FE} as follows.

В	С	D
60 to 120	100 to 200	160 to 320

See characteristic curves of 2SC1213.



Package Dimensions



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